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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	68
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p250-2vqg100

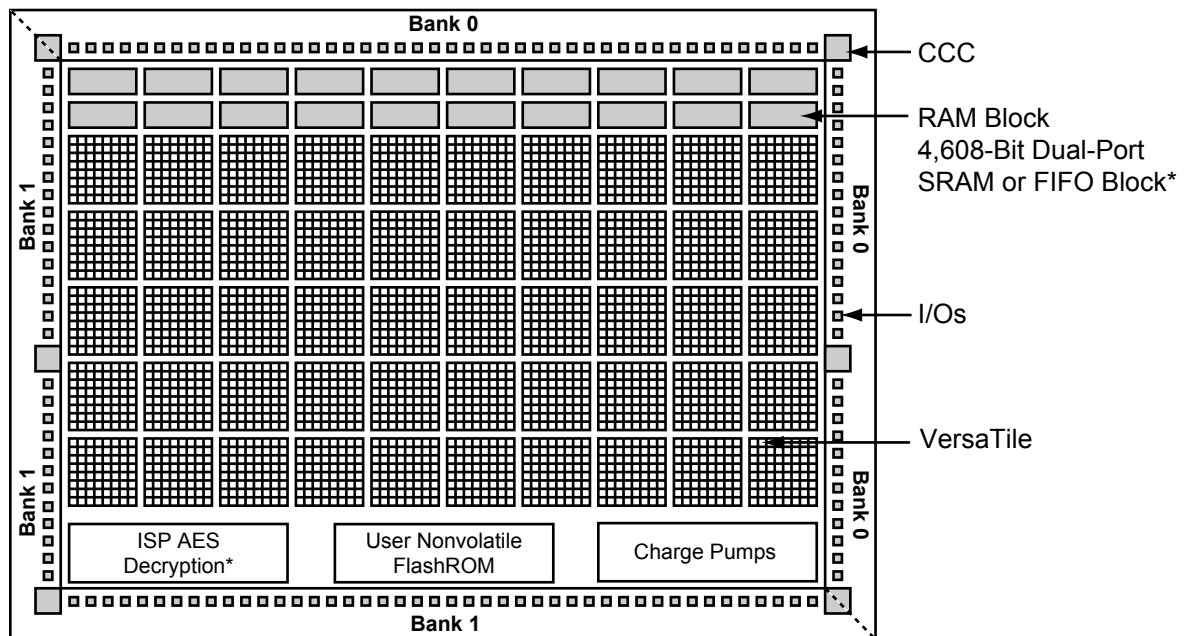
Advanced Flash Technology

The ProASIC3 family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVC MOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Advanced Architecture

The proprietary ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory[†]
- Extensive CCCs and PLLs[†]
- Advanced I/O structure



Note: *Not supported by A3P015 and A3P030 devices

Figure 1-1 • ProASIC3 Device Architecture Overview with Two I/O Banks (A3P015, A3P030, A3P060, and A3P125)

[†] The A3P015 and A3P030 do not support PLL or SRAM.

I/Os with Advanced I/O Standards

The ProASIC3 family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). ProASIC3 FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported ([Table 1-1](#)).

Table 1-1 • I/O Standards Supported

I/O Bank Type	Device and Bank Location	I/O Standards Supported		
		LVTTL/ LVCMOS	PCI/PCI-X	LVPECL, LVDS, B-LVDS, M-LVDS
Advanced	East and west Banks of A3P250 and larger devices	✓	✓	✓
Standard Plus	North and south banks of A3P250 and larger devices All banks of A3P060 and A3P125	✓	✓	Not supported
Standard	All banks of A3P015 and A3P030	✓	Not supported	Not supported

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

ProASIC3 banks for the A3P250 device and above support LVPECL, LVDS, B-LVDS and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Wide Range I/O Support

ProASIC3 devices support JEDEC-defined wide range I/O operation. ProASIC3 supports the JESD8-B specification, covering both 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the [FlashPro User's Guide](#) for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify ([Figure 1-4 on page 1-8](#)).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:
 - 1 – I/O is set to drive out logic High

Table 2-9 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings
Applicable to Standard Plus I/O Banks

	VMV (V)	Static Power PDC2 (mW) ¹	Dynamic Power PAC9 (μW/MHz) ²
2.5 V LVCMOS	2.5	–	5.14
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.48
3.3 V PCI	3.3	–	18.13
3.3 V PCI-X	3.3	–	18.13

Notes:

1. PDC2 is the static power (where applicable) measured on VMV.
2. PAC9 is the total dynamic power measured on VCC and VMV.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

Table 2-10 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings
Applicable to Standard I/O Banks

	VMV (V)	Static Power PDC2 (mW) ¹	Dynamic Power PAC9 (μW/MHz) ²
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	–	17.24
3.3 V LVCMOS Wide Range ³	3.3	–	17.24
2.5 V LVCMOS	2.5	–	5.19
1.8 V LVCMOS	1.8	–	2.18
1.5 V LVCMOS (JESD8-11)	1.5	–	1.52

Notes:

1. PDC2 is the static power (where applicable) measured on VMV.
2. PAC9 is the total dynamic power measured on VCC and VMV.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

P_{AC1} , P_{AC2} , P_{AC3} , and P_{AC4} are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution— $P_{OUTPUTS}$

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-16 on page 2-14](#).

β_1 is the I/O buffer enable rate—guidelines are provided in [Table 2-17 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

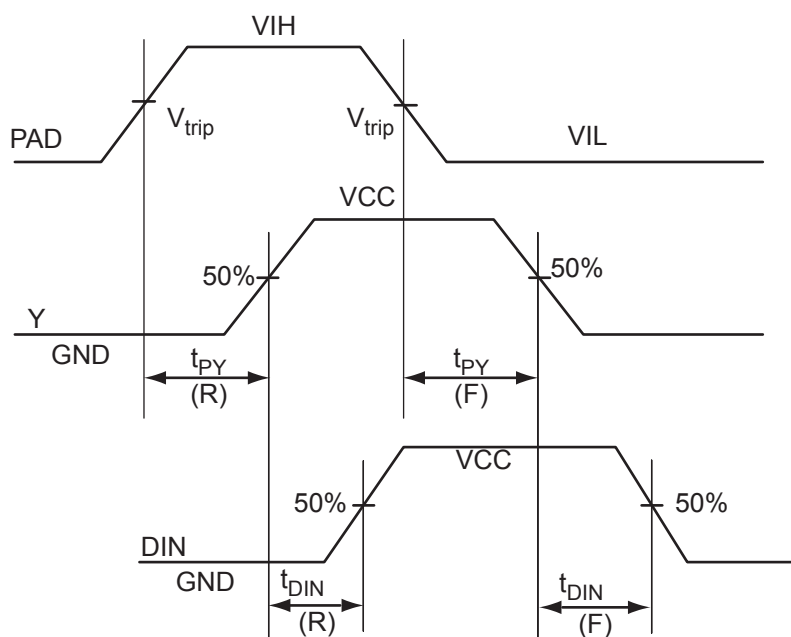
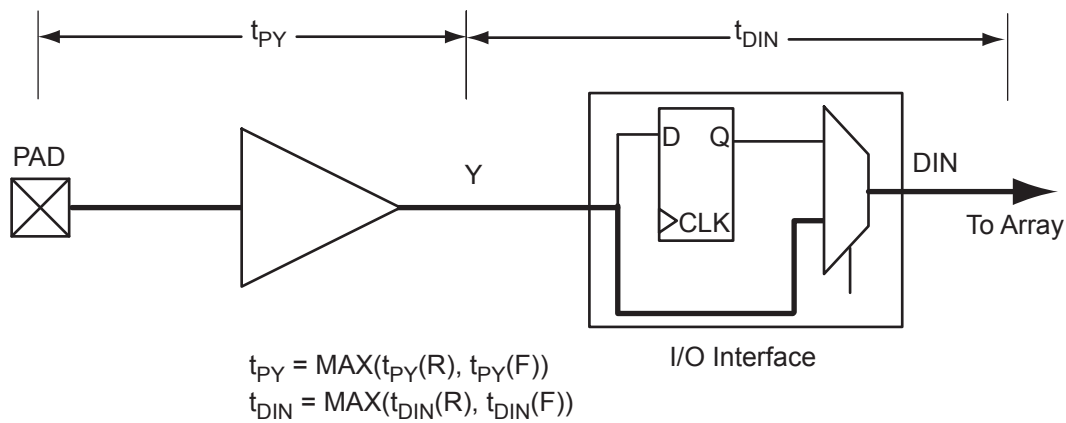


Figure 2-4 • Input Buffer Timing Model and Delays (Example)

I/O DC Characteristics

Table 2-27 • Input Capacitance

Symbol	Definition	Conditions	Min	Max	Units
C_{IN}	Input capacitance	$V_{IN} = 0$, $f = 1.0$ MHz	–	8	pF
C_{INCLK}	Input capacitance on the clock pin	$V_{IN} = 0$, $f = 1.0$ MHz	–	8	pF

Table 2-28 • I/O Output Buffer Maximum Resistances¹
Applicable to Advanced I/O Banks

Standard	Drive Strength	$R_{PULL-DOWN} (\Omega)^2$	$R_{PULL-UP} (\Omega)^3$
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range ⁴	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on V_{CCI} , drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL-UP-MAX)} = (V_{CCImax} - V_{OHspec}) / I_{OHspec}$
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

Single-Ended I/O Characteristics

3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer.

Table 2-37 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	–0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-38 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	109	103	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-45 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-46 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
4 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
6 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns
8 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-61 • 2.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	11.40	0.04	1.31	0.43	11.22	11.40	2.68	2.20	13.45	13.63	ns
	–1	0.51	9.69	0.04	1.11	0.36	9.54	9.69	2.28	1.88	11.44	11.60	ns
	–2	0.45	8.51	0.03	0.98	0.32	8.38	8.51	2.00	1.65	10.05	10.18	ns
6 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
8 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
12 mA	Std.	0.60	6.18	0.04	1.31	0.43	6.29	5.92	3.30	3.32	8.53	8.15	ns
	–1	0.51	5.26	0.04	1.11	0.36	5.35	5.03	2.81	2.83	7.26	6.94	ns
	–2	0.45	4.61	0.03	0.98	0.32	4.70	4.42	2.47	2.48	6.37	6.09	ns
16 mA	Std.	0.60	5.76	0.04	1.31	0.43	5.87	5.53	3.36	3.44	8.11	7.76	ns
	–1	0.51	4.90	0.04	1.11	0.36	4.99	4.70	2.86	2.92	6.90	6.60	ns
	–2	0.45	4.30	0.03	0.98	0.32	4.38	4.13	2.51	2.57	6.05	5.80	ns
24 mA	Std.	0.60	5.51	0.04	1.31	0.43	5.50	5.51	3.43	3.87	7.74	7.74	ns
	–1	0.51	4.68	0.04	1.11	0.36	4.68	4.68	2.92	3.29	6.58	6.59	ns
	–2	0.45	4.11	0.03	0.98	0.32	4.11	4.11	2.56	2.89	5.78	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-71 • 1.8 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	15.53	0.04	1.22	0.43	14.11	15.53	2.78	1.60	16.35	17.77	ns
	–1	0.56	13.21	0.04	1.04	0.36	12.01	13.21	2.36	1.36	13.91	15.11	ns
	–2	0.49	11.60	0.03	0.91	0.32	10.54	11.60	2.07	1.19	12.21	13.27	ns
4 mA	Std.	0.66	10.48	0.04	1.22	0.43	10.41	10.48	3.23	2.73	12.65	12.71	ns
	–1	0.56	8.91	0.04	1.04	0.36	8.86	8.91	2.75	2.33	10.76	10.81	ns
	–2	0.49	7.82	0.03	0.91	0.32	7.77	7.82	2.41	2.04	9.44	9.49	ns
6 mA	Std.	0.66	8.05	0.04	1.22	0.43	8.20	7.84	3.54	3.27	10.43	10.08	ns
	–1	0.56	6.85	0.04	1.04	0.36	6.97	6.67	3.01	2.78	8.88	8.57	ns
	–2	0.49	6.01	0.03	0.91	0.32	6.12	5.86	2.64	2.44	7.79	7.53	ns
8 mA	Std.	0.66	7.50	0.04	1.22	0.43	7.64	7.30	3.61	3.41	9.88	9.53	ns
	–1	0.56	6.38	0.04	1.04	0.36	6.50	6.21	3.07	2.90	8.40	8.11	ns
	–2	0.49	5.60	0.03	0.91	0.32	5.71	5.45	2.69	2.55	7.38	7.12	ns
12 mA	Std.	0.66	7.29	0.04	1.22	0.43	7.23	7.29	3.71	3.95	9.47	9.53	ns
	–1	0.56	6.20	0.04	1.04	0.36	6.15	6.20	3.15	3.36	8.06	8.11	ns
	–2	0.49	5.45	0.03	0.91	0.32	5.40	5.45	2.77	2.95	7.07	7.12	ns
16 mA	Std.	0.66	7.29	0.04	1.22	0.43	7.23	7.29	3.71	3.95	9.47	9.53	ns
	–1	0.56	6.20	0.04	1.04	0.36	6.15	6.20	3.15	3.36	8.06	8.11	ns
	–2	0.49	5.45	0.03	0.91	0.32	5.40	5.45	2.77	2.95	7.07	7.12	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-93 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-94 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)
1.64	1.94	Cross point

Note: *Measuring point = V_{trip} . See [Table 2-22 on page 2-22](#) for a complete table of trip points.

Timing Characteristics

Table 2-95 • LVPECL

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.66	1.80	0.04	1.40	ns
–1	0.56	1.53	0.04	1.19	ns
–2	0.49	1.34	0.03	1.05	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

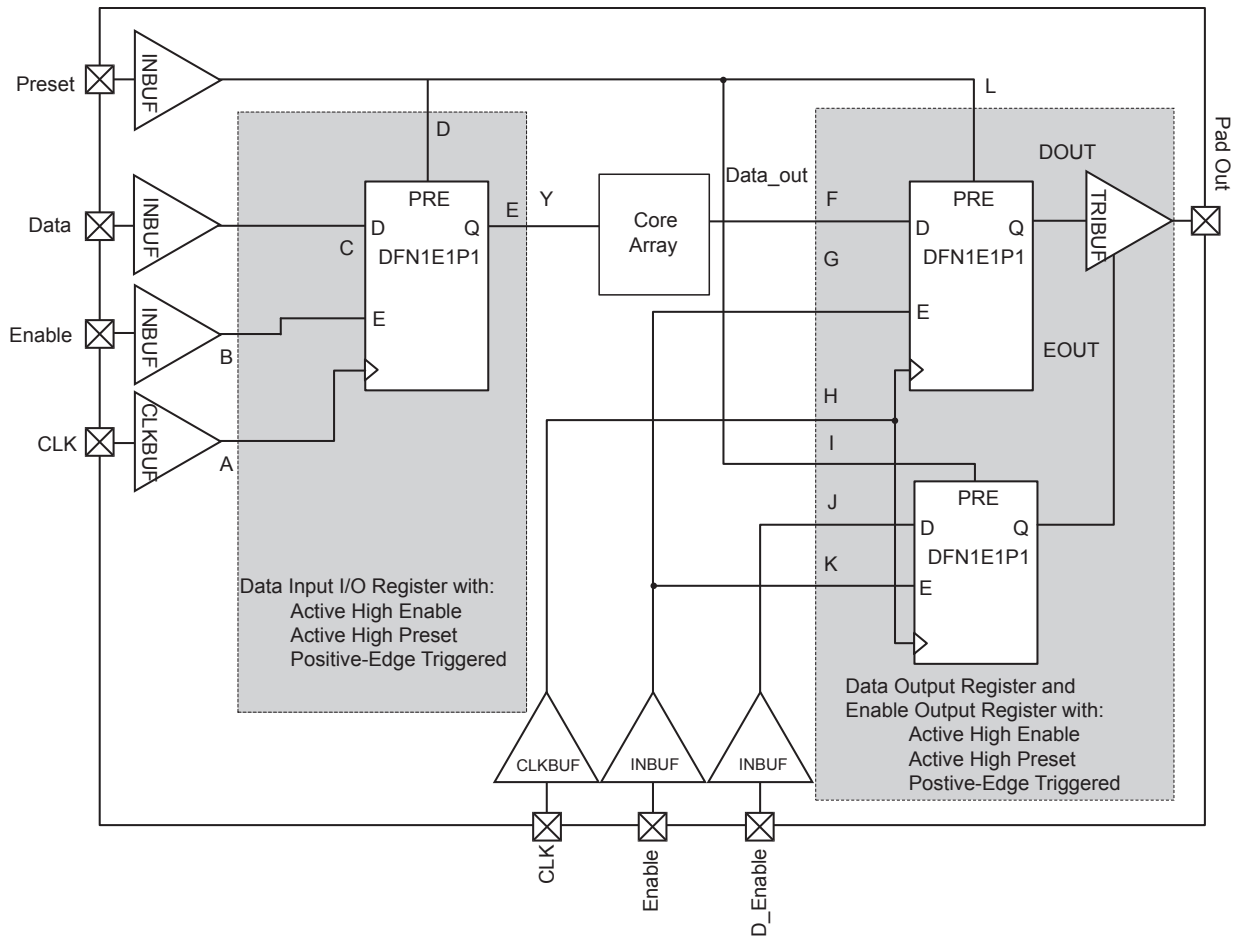


Figure 2-15 • Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

Table 2-96 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-15 on page 2-69 for more information.

Timing Characteristics

Table 2-116 • RAM4K9
Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BLK hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.36	2.68	3.15	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	1.79	2.03	2.39	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t_{C2CWWH}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

QN132	
Pin Number	A3P250 Function
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

PQ208	
Pin Number	A3P1000 Function
1	GND
2	GAA2/IO225PDB3
3	IO225NDB3
4	GAB2/IO224PDB3
5	IO224NDB3
6	GAC2/IO223PDB3
7	IO223NDB3
8	IO222PDB3
9	IO222NDB3
10	IO220PDB3
11	IO220NDB3
12	IO218PDB3
13	IO218NDB3
14	IO216PDB3
15	IO216NDB3
16	VCC
17	GND
18	VCCIB3
19	IO212PDB3
20	IO212NDB3
21	GFC1/IO209PDB3
22	GFC0/IO209NDB3
23	GFB1/IO208PDB3
24	GFB0/IO208NDB3
25	VCOMPLF
26	GFA0/IO207NPB3
27	VCCPLF
28	GFA1/IO207PPB3
29	GND
30	GFA2/IO206PDB3
31	IO206NDB3
32	GFB2/IO205PDB3
33	IO205NDB3
34	GFC2/IO204PDB3
35	IO204NDB3
36	VCC

PQ208	
Pin Number	A3P1000 Function
37	IO199PDB3
38	IO199NDB3
39	IO197PSB3
40	VCCIB3
41	GND
42	IO191PDB3
43	IO191NDB3
44	GEC1/IO190PDB3
45	GEC0/IO190NDB3
46	GEB1/IO189PDB3
47	GEB0/IO189NDB3
48	GEA1/IO188PDB3
49	GEA0/IO188NDB3
50	VMV3
51	GNDQ
52	GND
53	VMV2
54	GEA2/IO187RSB2
55	GEB2/IO186RSB2
56	GEC2/IO185RSB2
57	IO184RSB2
58	IO183RSB2
59	IO182RSB2
60	IO181RSB2
61	IO180RSB2
62	VCCIB2
63	IO178RSB2
64	IO176RSB2
65	GND
66	IO174RSB2
67	IO172RSB2
68	IO170RSB2
69	IO168RSB2
70	IO166RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P1000 Function
73	IO162RSB2
74	IO160RSB2
75	IO158RSB2
76	IO156RSB2
77	IO154RSB2
78	IO152RSB2
79	IO150RSB2
80	IO148RSB2
81	GND
82	IO143RSB2
83	IO141RSB2
84	IO139RSB2
85	IO137RSB2
86	IO135RSB2
87	IO133RSB2
88	VCC
89	VCCIB2
90	IO128RSB2
91	IO126RSB2
92	IO124RSB2
93	IO122RSB2
94	IO120RSB2
95	IO118RSB2
96	GDC2/IO116RSB2
97	GND
98	GDB2/IO115RSB2
99	GDA2/IO114RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	GNDQ
108	TDO

FG144	
Pin Number	A3P060 Function
K1	GEB0/IO74RSB1
K2	GEA1/IO73RSB1
K3	GEA0/IO72RSB1
K4	GEA2/IO71RSB1
K5	IO65RSB1
K6	IO64RSB1
K7	GND
K8	IO57RSB1
K9	GDC2/IO56RSB1
K10	GND
K11	GDA0/IO50RSB0
K12	GDB0/IO48RSB0
L1	GND
L2	VMV1
L3	GEB2/IO70RSB1
L4	IO67RSB1
L5	VCCIB1
L6	IO62RSB1
L7	IO59RSB1
L8	IO58RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO69RSB1
M3	IO68RSB1
M4	IO66RSB1
M5	IO63RSB1
M6	IO61RSB1
M7	IO60RSB1
M8	NC
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	A3P600 Function
G13	GCC1/IO69PPB1
G14	IO65NPB1
G15	IO75PDB1
G16	IO75NDB1
H1	GFB0/IO163NPB3
H2	GFA0/IO162NDB3
H3	GFB1/IO163PPB3
H4	VCOMPLF
H5	GFC0/IO164NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO69NPB1
H13	GCB1/IO70PPB1
H14	GCA0/IO71NPB1
H15	IO67NPB1
H16	GCB0/IO70NPB1
J1	GFA2/IO161PPB3
J2	GFA1/IO162PDB3
J3	VCCPLF
J4	IO160NDB3
J5	GFB2/IO160PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO73PPB1
J13	GCA1/IO71PPB1
J14	GCC2/IO74PPB1
J15	IO80PPB1
J16	GCA2/IO72PDB1

FG256	
Pin Number	A3P600 Function
K1	GFC2/IO159PDB3
K2	IO161NPB3
K3	IO156PPB3
K4	IO129RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO73NPB1
K14	IO80NPB1
K15	IO74NPB1
K16	IO72NDB1
L1	IO159NDB3
L2	IO156NPB3
L3	IO151PPB3
L4	IO158PSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO87NPB1
L14	IO85NDB1
L15	IO85PDB1
L16	IO84PDB1
M1	IO150PDB3
M2	IO151NPB3
M3	IO147NPB3
M4	GEC0/IO146NPB3

FG256	
Pin Number	A3P600 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO117RSB2
M9	IO110RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO94RSB2
M14	GDB1/IO87PPB1
M15	GDC1/IO86PDB1
M16	IO84NDB1
N1	IO150NDB3
N2	IO147PPB3
N3	GEC1/IO146PPB3
N4	IO140RSB2
N5	GNDQ
N6	GEA2/IO143RSB2
N7	IO126RSB2
N8	IO120RSB2
N9	IO108RSB2
N10	IO103RSB2
N11	IO99RSB2
N12	GNDQ
N13	IO92RSB2
N14	VJTAG
N15	GDC0/IO86NDB1
N16	GDA1/IO88PDB1
P1	GEB1/IO145PDB3
P2	GEB0/IO145NDB3
P3	VMV2
P4	IO138RSB2
P5	IO136RSB2
P6	IO131RSB2
P7	IO124RSB2
P8	IO119RSB2

FG484	
Pin Number	A3P600 Function
K19	IO75NDB1
K20	NC
K21	IO76NDB1
K22	IO76PDB1
L1	NC
L2	IO155PDB3
L3	NC
L4	GFB0/IO163NPB3
L5	GFA0/IO162NDB3
L6	GFB1/IO163PPB3
L7	VCOMPLF
L8	GFC0/IO164NPB3
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO69NPB1
L16	GCB1/IO70PPB1
L17	GCA0/IO71NPB1
L18	IO67NPB1
L19	GCB0/IO70NPB1
L20	IO77PDB1
L21	IO77NDB1
L22	IO78NPB1
M1	NC
M2	IO155NDB3
M3	IO158NPB3
M4	GFA2/IO161PPB3
M5	GFA1/IO162PDB3
M6	VCCPLF
M7	IO160NDB3
M8	GFB2/IO160PDB3
M9	VCC
M10	GND

FG484	
Pin Number	A3P600 Function
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO73PPB1
M16	GCA1/IO71PPB1
M17	GCC2/IO74PPB1
M18	IO80PPB1
M19	GCA2/IO72PDB1
M20	IO79PPB1
M21	IO78PPB1
M22	NC
N1	IO154NDB3
N2	IO154PDB3
N3	NC
N4	GFC2/IO159PDB3
N5	IO161NPB3
N6	IO156PPB3
N7	IO129RSB2
N8	VCCIB3
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB1
N16	IO73NPB1
N17	IO80NPB1
N18	IO74NPB1
N19	IO72NDB1
N20	NC
N21	IO79NPB1
N22	NC
P1	NC
P2	IO153PDB3

FG484	
Pin Number	A3P600 Function
P3	IO153NDB3
P4	IO159NDB3
P5	IO156NPB3
P6	IO151PPB3
P7	IO158PPB3
P8	VCCIB3
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB1
P16	GDB0/IO87NPB1
P17	IO85NDB1
P18	IO85PDB1
P19	IO84PDB1
P20	NC
P21	IO81PDB1
P22	NC
R1	NC
R2	NC
R3	VCC
R4	IO150PDB3
R5	IO151NPB3
R6	IO147NPB3
R7	GEC0/IO146NPB3
R8	VMV3
R9	VCCIB2
R10	VCCIB2
R11	IO117RSB2
R12	IO110RSB2
R13	VCCIB2
R14	VCCIB2
R15	VMV2
R16	IO94RSB2

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to 85°C .	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from 110°C to 100°C , with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1